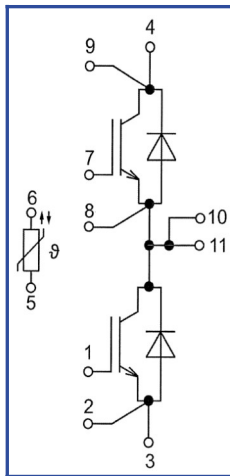
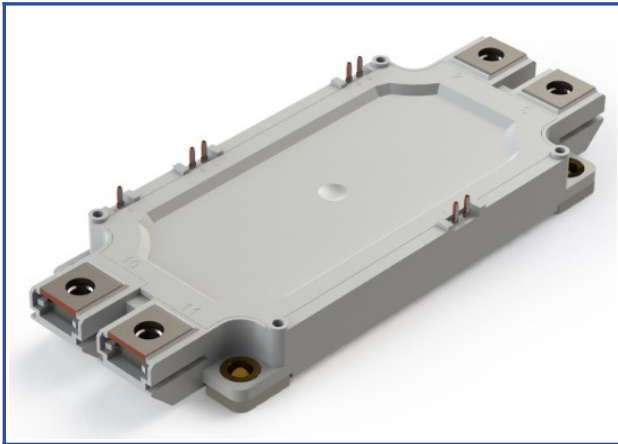


Low Inductance IGBT Module with 17 mm Height Housing
1700 V 300 A

Chip features

- IGBT chip
 - low $V_{CE(sat)}$ value
 - 10 μs short circuit duration at 150°C
 - square RBSOA of $2 \times I_c$
- FRD chip
 - fast and soft reverse recovery
 - low voltage drop

Design features

- copper baseplate
- Al_2O_3 DBC substrate
- ultrasonic welded power terminals
- improved thermal cycling
- RoHS compliant
- low inductance value

Typical application

- AC motor drives
- solar inverters
- air conditioning
- high power converters and UPS
- Inverters for wind energy converters

Maximum rated values

Definition	Symbol	Conditions	Value	Unit
IGBT				
Collector-Emitter voltage	V_{CES}	$V_{GE} = 0$.	1700	V
Maximum allowable collector current (continuous)	$I_{C 25}$	$T_{vj (max)} = 175^\circ C; T_c = 25^\circ C$.	-	A
	$I_{C 80}$	$T_{vj (max)} = 175^\circ C; T_c = 80^\circ C$.	300	A
Repetitive peak collector current*1	I_{CRM}	$I_{CRM} = 2 \times I_{C nom}; t_p = 1 ms$.	600	A
Short-circuit duration	t_{psc}	$T_{vj} = 25^\circ C; V_{GE} = \pm 15 V; V_{CE} = 700 V;$ $R_{G on} = R_{G off} = 3 \Omega$	10	μs
		$T_{vj} = 150^\circ C; V_{GE} = \pm 15 V; V_{CE} = 700 V;$ $R_{G on} = R_{G off} = 3 \Omega$	10	
Gate-Emitter voltage	V_{GES}		± 20	V
Junction operating temperature	$T_{vj (op)}$		-40...+150	°C
Inverse diode \ Freewheeling diode				
Repetitive peak reverse voltage	V_{RRM}	$V_{GE} = 0 V$.	1700	V
Maximum allowable forward current (continuous)	$I_{F 25}$	$T_{vj (max)} = 175^\circ C; T_c = 25^\circ C$.	-	A
	$I_{F 80}$	$T_{vj (max)} = 175^\circ C; T_c = 80^\circ C$.	300	A
Repetitive peak forward current*1	I_{FRM}	$I_{FRM} = 2 \times I_{F nom}; t_p = 1 ms$.	600	A
Junction operating temperature	$T_{vj (op)}$		-40...+150	°C
Module				
Storage temperature	T_{stg}		-40...+50	°C
Isolation voltage	V_{isol}	AC sin 50 Hz; t = 1 min.	4000	V

*1 Pulse width and repetition rate should be such that device junction temperature does not exceed maximum T_{vj} rating

Characteristics

Definition	Symbol	Conditions	Value			Unit	
			min.	typ.	max.		
IGBT							
Collector-Emitter saturation voltage	V_{CEsat}	$V_{GE} = +15\text{ V}; I_C = 300\text{ A}; t_u = 1000\text{ }\mu\text{s}.$	$T_{vj} = 25^\circ\text{C}$	-	2.55	-	V
			$T_{vj} = 150^\circ\text{C}$	-	3.15	-	V
Gate-Emitter threshold voltage	$V_{GE(th)}$	$I_C = 18\text{ mA}; V_{CE} = V_{GE}; T_{vj} = 25^\circ\text{C}; t_u = 2\text{ ms}.$		4.50	-	6.50	V
Collector-Emitter cut-off current	I_{CES}	$V_{CE} = 1700\text{ V}; t_u = 50\text{ ms}; V_{GE} = 0.$	$T_{vj} = 25^\circ\text{C}$	-	-	300	μA
			$T_{vj} = 150^\circ\text{C}$	-	5.00	-	mA
Gate-Emitter leakage current	I_{GES}	$V_{CE} = 0; V_{GE} = \pm 20\text{ V}; T_{vj} = 25^\circ\text{C}; t_u = 30\text{ ms}.$		-	-	500	nA
Input capacitance	C_{ies}	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V};$		-	18.30	-	nF
Reverse transfer capacitance	C_{res}	$f = 1\text{ MHz}; T_{vj} = 25^\circ\text{C}.$		-	0.72	-	nF
Total gate charge	Q_G	$I_{Cmax} = 300\text{ A}; V_{CE} = 920\text{ V}; V_{GE} = -8 \div 15\text{ V}.$		-	2100	-	nC
Internal gate resistance	R_{Gint}	$T_{vj} = 25^\circ\text{C}.$		-	2.00	-	Ω
Turn-on delay time	$t_{d(on)}$		$T_{vj} = 25^\circ\text{C}$	-	195	-	ns
			$T_{vj} = 150^\circ\text{C}$	-	208	-	ns
Rise time	t_{ri}	$V_{CE} = 920\text{ V}; V_{GE} = \pm 15\text{ V};$	$T_{vj} = 25^\circ\text{C}$	-	70	-	ns
			$T_{vj} = 150^\circ\text{C}$	-	78	-	ns
Turn-on energy	E_{on}	$I_{Cmax} = 300\text{ A}; R_G = 3\text{ }\Omega;$	$T_{vj} = 25^\circ\text{C}$	-	69.0	-	mJ
			$T_{vj} = 150^\circ\text{C}$	-	102.0	-	mJ
Turn-off delay time	$t_{d(off)}$	$L_s = 53\text{ nH}.$	$T_{vj} = 25^\circ\text{C}$	-	400	-	ns
			$T_{vj} = 150^\circ\text{C}$	-	520	-	ns
Fall time	t_{fi}		$T_{vj} = 25^\circ\text{C}$	-	160	-	ns
			$T_{vj} = 150^\circ\text{C}$	-	190	-	ns
Turn-off energy	E_{off}		$T_{vj} = 25^\circ\text{C}$	-	66.0	-	mJ
			$T_{vj} = 150^\circ\text{C}$	-	99.0	-	mJ
Collector-emitter threshold voltage	V_{CE0}	$V_{GE} = +15\text{ V}; T_{vj} = 150^\circ\text{C};$		-	-	-	V
On-State slope resistance (IGBT)	r_{CE0}	$I_{CE1} = 75\text{ A}; I_{CE2} = 300\text{ A}; t_u = 1000\text{ }\mu\text{s}.$		-	-	-	$\text{m}\Omega$
Thermal resistance junction to case	$R_{th(j-c)}$	DC; $I_{CE} = 250 \pm 50\text{ A}; I_{test} = 1.5\text{ A}; V_{GE} = +15\text{ V}.$		-	-	0.075	K/W
Inverse diode \ Freewheeling diode							
Forward voltage drop	V_F	$I_F = 300\text{ A}; V_{GE} = 0; t_u = 1000\text{ }\mu\text{s}.$	$T_{vj} = 25^\circ\text{C}$	-	1.95	-	V
			$T_{vj} = 150^\circ\text{C}$	-	2.20	-	V
Reverse recovery time	t_{rr}		$T_{vj} = 25^\circ\text{C}$	-	500	-	ns
			$T_{vj} = 150^\circ\text{C}$	-	680	-	ns
Peak reverse current	I_{RM}	$V_{GE} = \pm 15\text{ V}; V_{CE} = 920\text{ V}; I_{Cmax} = 300\text{ A};$	$T_{vj} = 25^\circ\text{C}$	-	350	-	A
			$T_{vj} = 150^\circ\text{C}$	-	400	-	A
Recovered charge	Q_r	$R_{Gon} = 3\text{ }\Omega; L_s = 53\text{ nH}.$	$T_{vj} = 25^\circ\text{C}$	-	90.0	-	μC
			$T_{vj} = 150^\circ\text{C}$	-	150.0	-	μC
Reverse recovery energy	E_{rec}		$T_{vj} = 25^\circ\text{C}$	-	57.0	-	mJ
			$T_{vj} = 150^\circ\text{C}$	-	95.0	-	mJ
Threshold voltage	$V_{(T0)}$	$T_{vj} = 150^\circ\text{C}; V_{GE} = 0; I_{CE1} = 75\text{ A};$		-	-	-	V
Forward slope resistance	r_T	$I_{CE2} = 300\text{ A}; t_u = 1000\text{ }\mu\text{s}$		-	-	-	$\text{m}\Omega$
Thermal resistance junction to case	$R_{th(jc-D)}$	DC; $I_{CE} = 250 \pm 50\text{ A}; I_{test} = 1.5\text{ A}; V_{GE} = +15\text{ V}.$		-	-	0.150	K/W

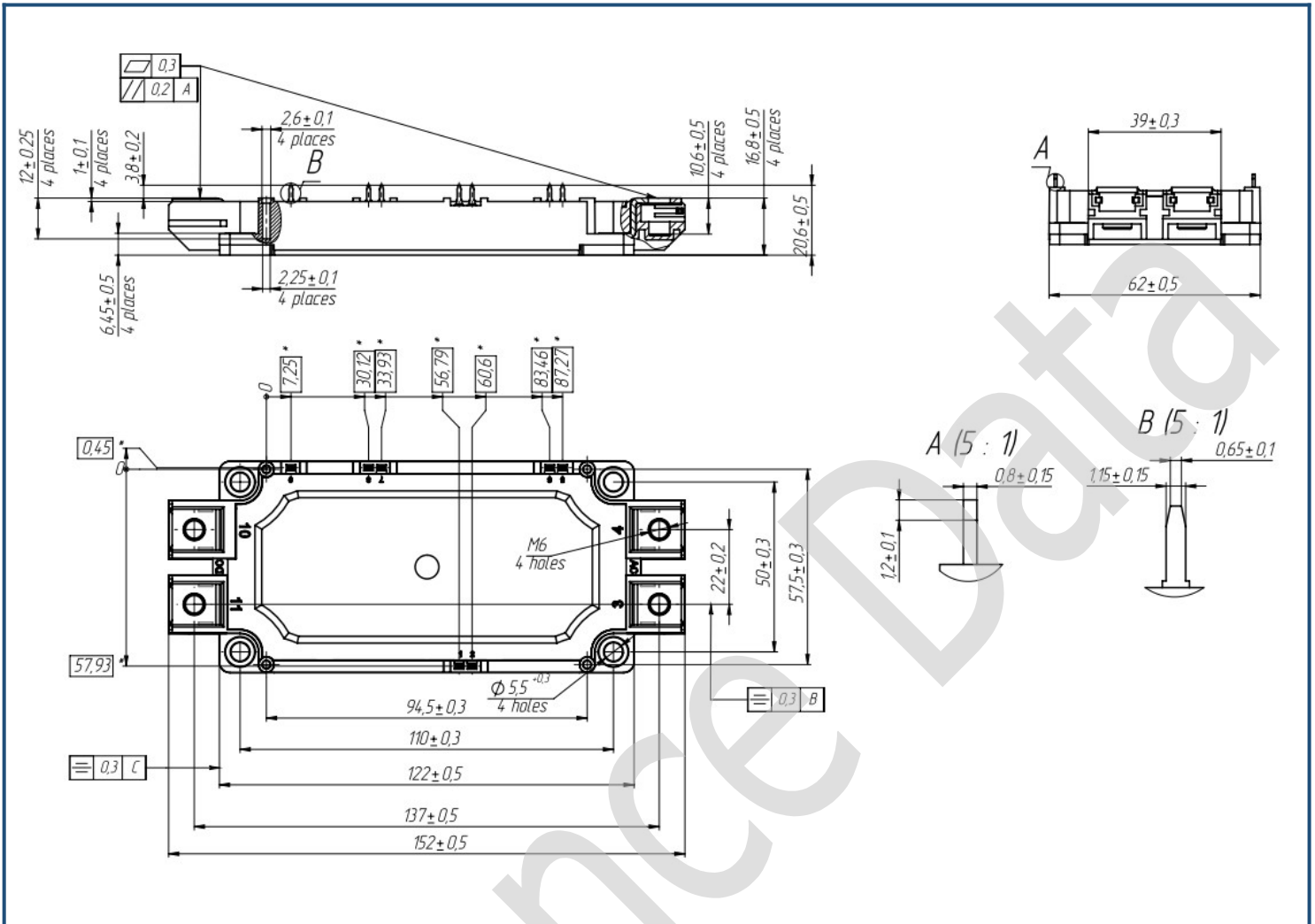
Module							
Pin resistance	R_{Pxy}	$T_{vj} = 25^{\circ}\text{C}$.	$R_{P10/11-3}$	-	0.92	1.00	m Ω
			$R_{P10/11-4}$	-	0.59	1.00	
Parasitic inductance between terminals	L_{Pce}			-	26	-	nH
Thermistor resistance	R_t	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$		4850	-	6225	Ω
				475	-	554	
Thermal resistance case to heatsink	R_{thCH}	per module		-	0.009	0.014	K/W
Mounting torque for screws to heatsink	M_s	to heatsink M5		3	-	6	N*m
Mounting torque for terminal screws	M_t	to terminals M6		3	-	6	N*m
Weight	W			-	360	-	g

" - " — data will be refined as additional tests are conducted and statistics are collected.

Notes:

- Insulating material operating temperature 125°C max;
- Case temperature 125°C max;
- The recommended operating junction temperature $T_{vj\ op} = -40\dots+150^{\circ}\text{C}$.

Overall dimensions: Package type – DA



Part numbering guide

MIDA	-	HB	17	AB	-	300	N	
MIDA								IGBT module package type: DA
		HB						Half-Bridge
			17					Voltage rating ($V_{CES}/100$)
				AB				IGBT+FRD chipset modification
						300		Current Rating
							N	Climatic version: normal climate

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